

Optoelectronic devices

Photo transistors

Type	Group	Fig. Nr.	Maximum ratings		Characteristics – electrical + optical				Spectral curve (see page 71)
			P_{tot} at $t_{amb} = +25^\circ C$ W	U_{CEO} V	α	$I_{ca}^{1)}$ mA	$t_r^{2)}$ at $U_S = 5 V, R_L = 100 \Omega$ μs	$t_f^{2)}$ μs	
BPW 13	A	21	0.375	32	80°	0.2...0.4	1.6	1.7	1
	B	21	0.375	32	80°	0.3...0.6	1.6	1.7	1
	C	21	0.375	32	80°	> 0.5	1.6	1.7	1
BPW 14	A	22	0.375	32	25°	2...4	1.6	1.7	1
	B	22	0.375	32	25°	3...6	1.6	1.7	1
	C	22	0.375	32	25°	> 5.0	1.6	1.7	1
BPW 16		23	0.05	32	80°	0.4	1.6	1.7	1
BPW 17		24	0.05	32	25°	3.0	1.6	1.7	1
BPW 29	A	25	0.25	32	30°	> 1.0 ³⁾	3.2	3.8	1
	B	25	0.25	32	30°	> 1.5 ³⁾	3.2	3.8	1
	C	25	0.25	32	30°	> 2.0 ³⁾	3.2	3.8	1

Remarks: ¹⁾ $E_A = 1 \text{ klx}$; ²⁾ $I_C = 1 \text{ mA}$, GaAs diode as emitter; ³⁾ $E_A = 100 \text{ lx}$

Data book reference: B 2 A

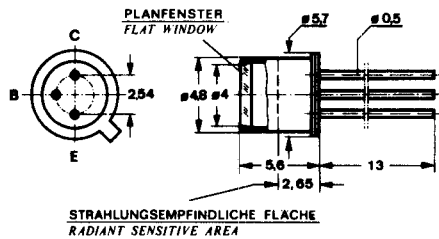


Fig. 21: 18 A 3 DIN 41876
JEDEC TO 18

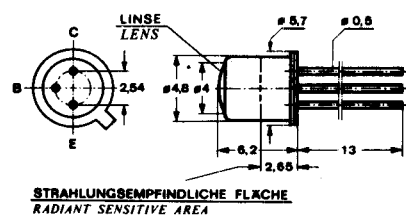


Fig. 22: 18 C 3 DIN 41876
≈ JEDEC TO 18

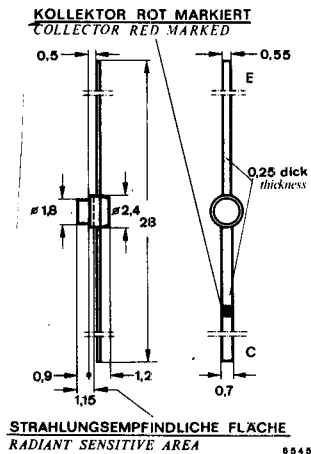


Fig. 23: Plastic case

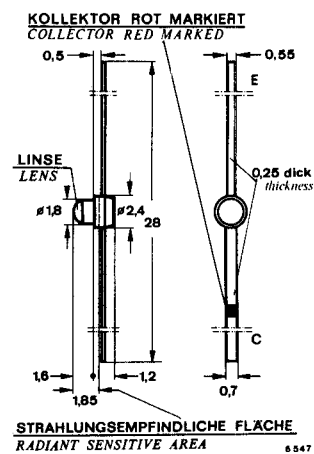


Fig. 24: Plastic case

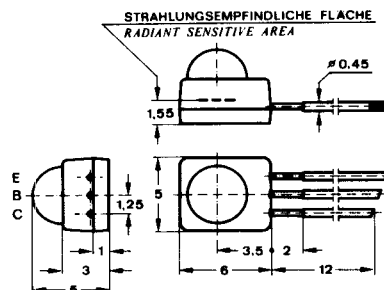


Fig. 25: Plastic case
≈ 10 B 3 DIN 41868
≈ JEDEC TO 92